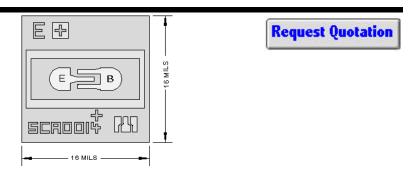




Chip Type 2C4261 Geometry 0014 Polarity PNP

Generic Packaged Parts:

2N4260, 2N4261



Chip type **2C4261** by Semicoa Semiconductors provides performance similar to these devices.

Product Summary:

APPLICATIONS:

Designed for low voltage, low gain RF amplifier applications.

Part Numbers:

2N4261, 2N4261UB, 2N4260, 2N4260UB, SD4261, SD4261F, SQ4261, SQ4261F

Features: Special Characteristics

ft = 1.8 GHz (typ) at 10 mA/10V

Mechanical Specifications				
Metallization	Тор	Al - 12 kÅ min.		
	Backside	Au - 6.5 kÅ nom.		
Bonding Pad Size	Emitter	2.1 mils x 2.1 mils		
	Base	2.1 mils x 2.1 mils		
Die Thickness	8 mils nominal			
Chip Area	16 mils x 16 mils			
Top Surface	Silox Passivated			

Electrical Characteristics T _A = 25°C						
Parameter	Test conditions	Min	Max	Unit		
BV _{CEO}	$I_{\rm C} = 10.0 \text{mA}, I_{\rm B} = 0$	15		V dc		
BV _{CBO}	$I_{C} = 10 \mu A, I_{E} = 0$	15		V dc		
BV _{EBO}	$I_E = 10 \mu A, I_C = 0$	4.5		V dc		
h _{FE}	$I_C = 10 \text{ mA dc}, V_{CE} = 1.0 \text{ V dc}$	30	150			

Due to limitations of probe testing, only dc parameters are tested. This must be done with pulse width less than 300 µs, duty cycle less than 2%.